

## Silicon PNP Power Transistors

2SA1490

## DESCRIPTION

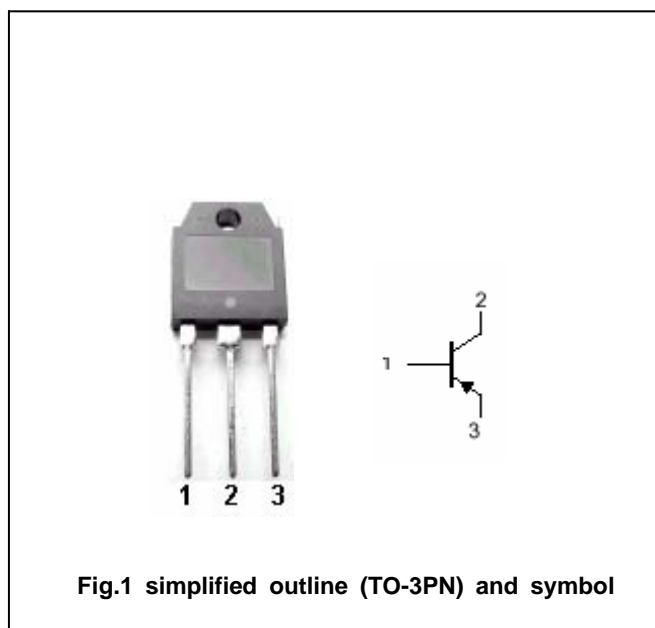
- With TO-3PN package
- Complement to type 2SC3854

## APPLICATIONS

- Audio and general purpose

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a = ^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-120	V
$V_{CEO}$	Collector-emitter voltage	Open base	-120	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-8	A
$I_B$	Base current		-3	A
$P_C$	Collector power dissipation	$T_C = 25^\circ\text{C}$	80	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-50mA ; I <sub>B</sub> =0	-120			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V	50			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =-12V		20		MHz

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =-4A; R <sub>L</sub> =10 Ω I <sub>B1</sub> =-I <sub>B2</sub> =-0.4A V <sub>CC</sub> =40V		0.25		μ s
t <sub>s</sub>	Storage time			0.7		μ s
t <sub>f</sub>	Fall time			0.2		μ s

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PACKAGE OUTLINE

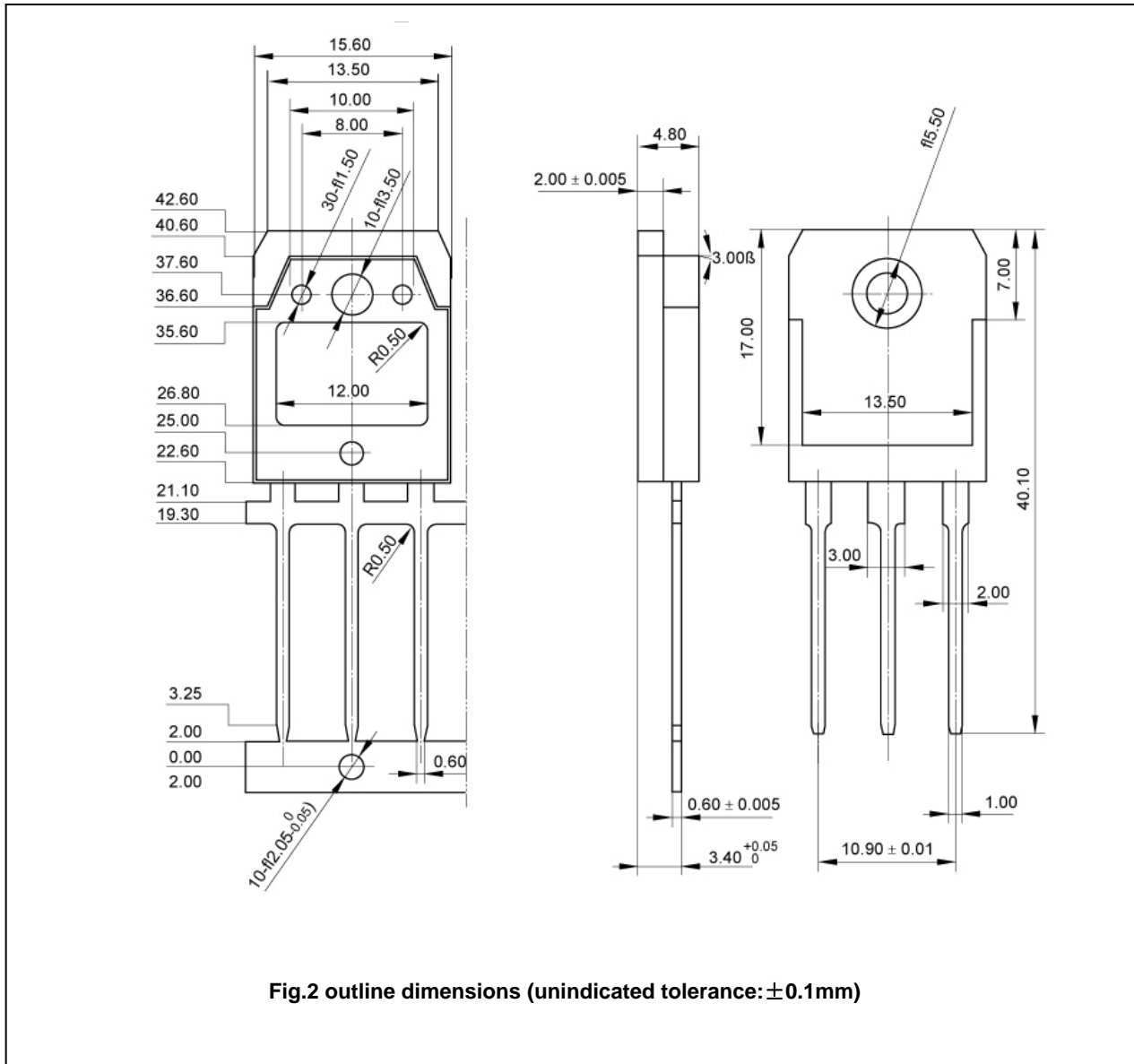


Fig.2 outline dimensions (unindicated tolerance: ±0.1mm)